SiT8009B

High Frequency, Low Power Oscillator



Features

- 100% pin-to-pin drop-in replacement to quartz-based XO
- Excellent total frequency stability as low as ±20 ppm
- Operating temperature from -40°C to 85°C. For 125°C and/or -55°C options, refer to SiT8919 and SiT8921
- Low power consumption of 4.9 mA typical at 1.8 V
- Standby mode for longer battery life
- Fast startup time of 5 ms
- LVCMOS/HCMOS compatible output
- Industry-standard packages: 2.0 x 1.6, 2.5 x 2.0, 3.2 x 2.5, 5.0 x 3.2, 7.0 x 5.0 mm x mm
- Instant samples with Time Machine II and field programmable oscillators
- RoHS and REACH compliant, Pb-free, Halogen-free and Antimony-free

Applications

- Ideal for GPON/EPON, network switches, routers. servers, embedded systems
- Ideal for Ethernet, PCI-E, DDR, etc.

Related products for automotive applications.

For aerospace and defense applications SiTime recommends using only Endura™ SiT8945.





SiTimeDirect



solutions



warranty

d field program-

■ For AEC-Q100 oscillators, refer to SiT8924 and SiT8925

Electrical Characteristics

All Min and Max limits are specified over temperature and rated operating voltage with 15 pF output load unless otherwise stated. Typical values are at 25°C and nominal supply voltage.

Table 1. Electrical Characteristics

Parameters	Symbol	Min.	Тур.	Max.	Unit	Condition
				Frequency F	Range	
Output Frequency Range	f	115	_	137	MHz	
			Freque	ncy Stabilit	y and Agin	g
Frequency Stability	F_stab	-20	-	+20	ppm	Inclusive of Initial tolerance at 25°C, 1st year aging at 25°C,
		-25	-	+25	ppm	and variations over operating temperature, rated power supply voltage and load.
		-50	-	+50	ppm	Supply voltage and load.
			Operat	ing Temper	ature Rang	e
Operating Temperature Range	T_use	-20	-	+70	°C	Extended Commercial
		-40	_	+85	°C	Industrial
		S	upply Volta	ge and Cur	rent Consu	mption
Supply Voltage	Vdd	1.62	1.8	1.98	V	Contact SiTime for 1.5 V support
		2.25	2.5	2.75	V	
		2.52	2.8	3.08	V	
		2.7	3.0	3.3	V	
		2.97	3.3	3.63	V	
		2.25	-	3.63	V	
Current Consumption	Idd	1	6.2	7.5	mA	No load condition, f = 125 MHz, Vdd = 2.8 V, 3.0 V, 3.3 V or 2.25 to 3.63 V
		-	5.5	6.4	mA	No load condition, f = 125 MHz, Vdd = 2.5 V
		Ī	4.9	5.6	mA	No load condition, f = 125 MHz, Vdd = 1.8 V
OE Disable Current	I_OD	-	_	4.2	mA	Vdd = 2.5 V to 3.3 V, OE = GND, Output in high-Z state
		-	_	4.0	mA	Vdd = 1.8 V, OE = GND, Output in high-Z state
Standby Current	I_std	Ī	2.6	4.3	μΑ	ST = GND, Vdd = 2.8 V to 3.3 V, Output is weakly pulled down
		-	1.4	2.5	μΑ	ST = GND, Vdd = 2.5 V, Output is weakly pulled down
		-	0.6	1.3	μА	ST = GND, Vdd = 1.8 V, Output is weakly pulled down
	•		LVCMO	S Output Cl	naracteristi	cs
Duty Cycle	DC	45	-	55	%	All Vdds
Rise/Fall Time	Tr, Tf	-	1	2	ns	Vdd = 2.5 V, 2.8 V, 3.0 V or 3.3 V, 20% - 80%
		-	1.3	2.5	ns	Vdd =1.8 V, 20% - 80%
		-	0.8	2	ns	Vdd = 2.25 V - 3.63 V, 20% - 80%
Output High Voltage	VOH	90%	-	-	Vdd	IOH = -4 mA (Vdd = 3.0 V or 3.3 V)
Output Low Voltage	VOL	-	_	10%	Vdd	IOL = 4 mA (Vdd = 3.0 V or 3.3 V)



Table 1. Electrical Characteristics (continued)

Parameters	Symbol	Min.	Тур.	Max.	Unit	Condition	
			Inp	ut Charact	eristics		
Input High Voltage	VIH	70%	_	_	Vdd	Pin 1, OE or ST	
Input Low Voltage	VIL	-	-	30%	Vdd	Pin 1, OE or ST	
Input Pull-up Impedance	Z_in	50	87	150	kΩ	Pin 1, OE logic high or logic low, or ST logic high	
		2	_	_	ΜΩ	Pin 1, ST logic low	
Startup and Resume Timing							
Startup Time	T_start	-	_	5	ms	Measured from the time Vdd reaches its rated minimum value	
Enable/Disable Time	T_oe	-	-	122	ns	f = 137 MHz. For other frequencies, T_oe = 100 ns + 3 * cycles	
Resume Time	T_resume	-	_	5	ms	Measured from the time ST pin crosses 50% threshold	
				Jitter			
RMS Period Jitter	T_jitt	-	1.9	3	ps	f = 125 MHz, Vdd = 2.5 V, 2.8 V, 3.0 V or 3.3 V	
		_	1.8	4	ps	f = 125 MHz, Vdd = 1.8 V	
Peak-to-peak Period Jitter	T_pk	_	12	25	ps	f = 125 MHz, Vdd = 2.5 V, 2.8 V, 3.0 V or 3.3 V	
		_	14	30	ps	f = 125 MHz, Vdd = 1.8 V	
RMS Phase Jitter (random)	T_phj	_	0.5	0.9	ps	Integration bandwidth = 900 kHz to 7.5 MHz	
		-	1.3	2	ps	Integration bandwidth = 12 kHz to 20 MHz	

Table 2. Pin Description

Pin	Symbol		Functionality
		Output Enable	H ^[1] : specified frequency output L: output is high impedance. Only output driver is disabled.
			H ^[1] : specified frequency output
1 OE/ST/NC	Standby	L: output is low (weak pull down). Device goes to sleep mode. Supply current reduces to I_std.	
		No Connect	Any voltage between 0 and Vdd or Open ^[1] : Specified frequency output. Pin 1 has no function.
2	GND	Power	Electrical ground
3	OUT	Output	Oscillator output
4	VDD	Power	Power supply voltage ^[2]

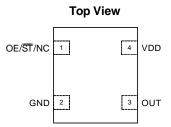


Figure 1. Pin Assignments

Notes:

- 1. In OE or \overline{ST} mode, a pull-up resistor of 10 k Ω or less is recommended if pin 1 is not externally driven. If pin 1 needs to be left floating, use the NC option.
- 2. A capacitor of value 0.1 μF or higher between Vdd and GND is required.



Table 3. Absolute Maximum Limits

Attempted operation outside the absolute maximum ratings may cause permanent damage to the part. Actual performance of the IC is only guaranteed within the operational specifications, not at absolute maximum ratings.

Parameter	Min.	Max.	Unit
Storage Temperature	-65	150	°C
Vdd	-0.5	4	V
Electrostatic Discharge	-	2000	V
Soldering Temperature (follow standard Pb free soldering guidelines)	_	260	°C
Junction Temperature ^[3]	_	150	°C

Note:

Table 4. Thermal Consideration[4]

Package	θJA, 4 Layer Board (°C/W)	θJA, 2 Layer Board (°C/W)	θJC, Bottom (°C/W)
7050	142	273	30
5032	97	199	24
3225	109	212	27
2520	117	222	26
2016	152	252	36

Note:

Table 5. Maximum Operating Junction Temperature^[5]

Max Operating Temperature (ambient)	Maximum Operating Junction Temperature		
70°C	80°C		
85°C	95°C		

Note:

5. Datasheet specifications are not guaranteed if junction temperature exceeds the maximum operating junction temperature.

Table 6. Environmental Compliance

Parameter	Condition/Test Method			
Mechanical Shock MIL-STD-883F, Method 2002				
Mechanical Vibration	MIL-STD-883F, Method 2007			
Temperature Cycle	JESD22, Method A104			
Solderability	MIL-STD-883F, Method2003			
Moisture Sensitivity Level	MSL1 @ 260°C			

^{3.} Exceeding this temperature for extended period of time may damage the device.

^{4.} Refer to JESD51 for θ JA and θ JC definitions, and reference layout used to determine the θ JA and θ JC values in the above table.



Test Circuit and Waveform[6]

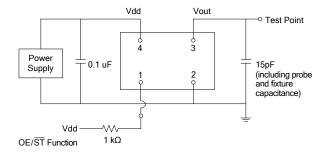


Figure 2. Test Circuit

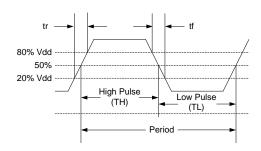


Figure 3. Waveform

Note:

6. Duty Cycle is computed as Duty Cycle =TH/Period.

Timing Diagrams

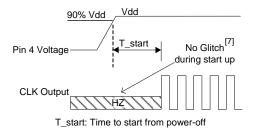


Figure 4. Startup Timing (OE/ST Mode)

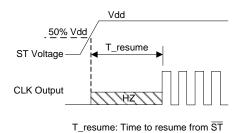


Figure 5. Standby Resume Timing (ST Mode Only)

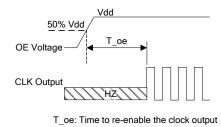


Figure 6. OE Enable Timing (OE Mode Only)

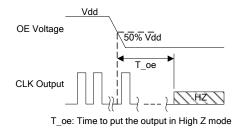


Figure 7. OE Disable Timing (OE Mode Only)

Note:
7. SiT8009 has "no runt" pulses and "no glitch" output during startup or resume.



Performance Plots[8]

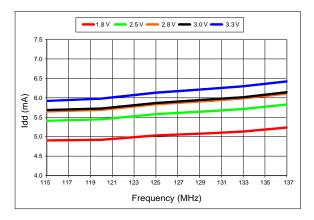


Figure 8. Idd vs Frequency

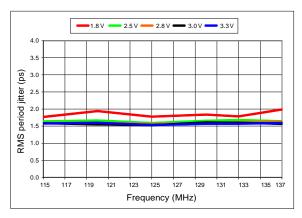


Figure 10. RMS Period Jitter vs Frequency

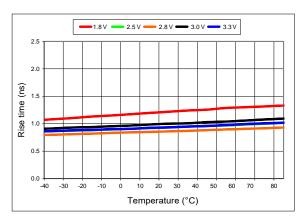


Figure 12. 20%-80% Rise Time vs Temperature

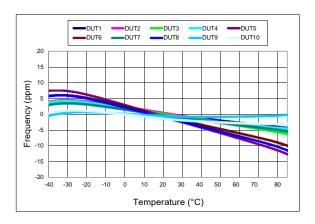


Figure 9. Frequency vs Temperature, 1.8 V

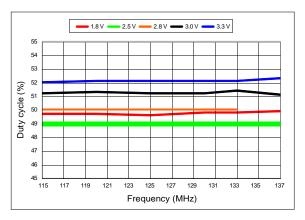


Figure 11. Duty Cycle vs Frequency

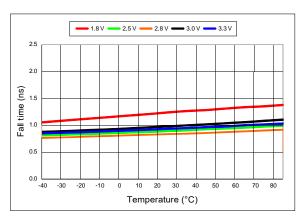
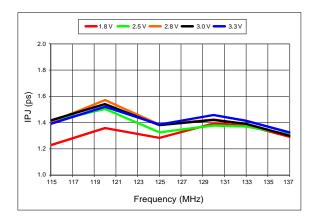


Figure 13. 20%-80% Fall Time vs Temperature



Performance Plots[8]



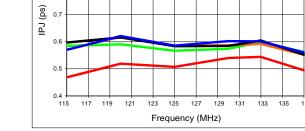


Figure 14. RMS Integrated Phase Jitter Random (12 kHz to 20 MHz) vs Frequency^[9]

Figure 15. RMS Integrated Phase Jitter Random (900 kHz to 20 MHz) vs Frequency^[9]

2.8 V - 3.0 V - 3.3 V

Notes:

- 8. All plots are measured with 15 pF load at room temperature, unless otherwise stated.
- 9. Phase noise plots are measured with Agilent E5052B signal source analyzer. Integration range is up to 5 MHz for carrier frequencies below 40 MHz.

0.9

0.8



Programmable Drive Strength

The SiT8009 includes a programmable drive strength feature to provide a simple, flexible tool to optimize the clock rise/fall time for specific applications. Benefits from the programmable drive strength feature are:

- Improves system radiated electromagnetic interference (EMI) by slowing down the clock rise/fall time
- Improves the downstream clock receiver's (RX) jitter by decreasing (speeding up) the clock rise/fall time.
- Ability to drive large capacitive loads while maintaining full swing with sharp edge rates.

For more detailed information about rise/fall time control and drive strength selection, see the SiTime Application Notes section.

EMI Reduction by Slowing Rise/Fall Time

Figure 16 shows the harmonic power reduction as the rise/fall times are increased (slowed down). The rise/fall times are expressed as a ratio of the clock period. For the ratio of 0.05, the signal is very close to a square wave. For the ratio of 0.45, the rise/fall times are very close to near-triangular waveform. These results, for example, show that the 11th clock harmonic can be reduced by 35 dB if the rise/fall edge is increased from 5% of the period to 45% of the period.

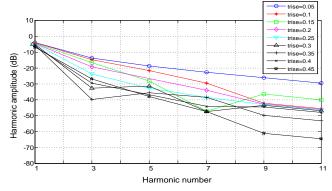


Figure 16. Harmonic EMI reduction as a Function of Slower Rise/Fall Time

Jitter Reduction with Faster Rise/Fall Time

Power supply noise can be a source of jitter for the downstream chipset. One way to reduce this jitter is to speed up the rise/fall time of the input clock. Some chipsets may also require faster rise/fall time in order to reduce their sensitivity to this type of jitter. Refer to the Rise/Fall Time Tables (Table 7 to Table 11) to determine the proper drive strength.

High Output Load Capability

The rise/fall time of the input clock varies as a function of the actual capacitive load the clock drives. At any given drive strength, the rise/fall time becomes slower as the output load increases. As an example, for a 3.3 V SiT8009 device with default drive strength setting, the typical rise/fall time is 0.46 ns for 5 pF output load. The typical rise/fall time slows down to 1 ns when the output load increases to 15 pF. One can choose to speed up the rise/fall time to 0.72 ns by then increasing the driven strength setting on the SiT8009 to "F".

The SiT8009 can support up to 30 pF or higher in maximum capacitive loads with up to 3 additional drive strength settings. Refer to the Rise/Fall Time Tables (Table 7 to 11) to determine the proper drive strength for the desired combination of output load vs. rise/fall time.

SiT8009 Drive Strength Selection

Tables 7 through 11 define the rise/fall time for a given capacitive load and supply voltage.

- 1. Select the table that matches the SiT8009 nominal supply voltage (1.8 V, 2.5 V, 2.8 V, 3.0 V, 3.3 V).
- 2. Select the capacitive load column that matches the application requirement (5 pF to 30 pF)
- 3. Under the capacitive load column, select the desired rise/fall times.
- The left-most column represents the part number code for the corresponding drive strength.
- **5.** Add the drive strength code to the part number for ordering purposes.

Calculating Maximum Frequency

Based on the rise and fall time data given in Table 7 through 11, the maximum frequency the oscillator can operate with guaranteed full swing of the output voltage over temperature as follows:

Max Frequency =
$$\frac{1}{5 \times \text{Trf } 20/80}$$

where Trf 20/80 is the typical value for 20%-80% rise/fall time.

Example 1

Calculate f_{MAX} for the following condition:

- Vdd = 3.3 V (Table 11)
- Capacitive Load: 30 pF
- Desired Tr/f time = 1.46 ns (rise/fall time part number code = U)

Part number for the above example:

SiT8009BIU12-33E-136.986300



Drive strength code is inserted here. Default setting is "-"



Rise/Fall Time (20% to 80%) vs CLOAD Tables

Table 7. Vdd = 1.8 V Rise/Fall Times for Specific C_{LOAD}

Rise/Fall Time Typ (ns)					
Drive Strength \C _{LOAD}	5 pF	15 pF	30 pF		
Т	0.93	n/	n/a		
E	0.78	n/	n/a		
U	0.70	1.4	n/a		
F or "-": default	0.65	1.3	n/a		

Table 9. Vdd = 2.8 V Rise/Fall Times for Specific C_{LOAD}

Rise/Fall Time Typ (ns)					
Drive Strength \ C _{LOAD}	5 pF	15 pF	30 pF		
R	1.29	n/a	n/a		
В	0.97	n/a	n/a		
Т	0.55	1.12	n/a		
E	0.44	1.00	n/a		
U or "-": default	0.34	0.88	n/a		
F	0.29	0.81	1.48		

Table 11. Vdd = 3.3 V Rise/Fall Times for Specific C_{LOAD}

Rise/Fall Time Typ (ns)					
Drive Strength \ C _{LOAD}	5 pF	15 pF	30 pF		
R	1.16	n/a	n/a		
В	0.81	n/a	n/a		
T or "-": default	0.46	1.00	n/a		
E	0.33	0.87	n/a		
U	0.28	0.79	1.46		
F	0.25	0.72	1.31		

Table 8. Vdd = 2.5 V Rise/Fall Times for Specific C_{LOAD}

Rise/Fall Time Typ (ns)					
Drive Strength \C _{LOAD}	5 pF	15 pF	30 pF		
R	1.45	n/a	n/a		
В	1.09	n/a	n/a		
Т	0.62	1.28	n/a		
E	0.54	1.00	n/a		
U or "-": default	0.43	0.96	n/a		
F	0.34	0.88	n/a		

Table 10. Vdd = 3.0 V Rise/Fall Times for Specific C_{LOAD}

Rise/Fall Time Typ (ns)					
Drive Strength \ C _{LOAD}	5 pF	15 pF	30 pF		
R	1.22	n/a	n/a		
В	0.89	n/a	n/a		
T or "-": default	0.51	1.00	n/a		
E	0.38	0.92	n/a		
U	0.30	0.83	n/a		
F	0.27	0.76	1.39		

Note:

^{10. &}quot;n/a" in Table 7 to Table 11indicates that the resulting rise/fall time from the respective combination of the drive strength and output load does not provide rail-to-rail swing and is not available.



Pin 1 Configuration Options (OE, ST, or NC)

Pin 1 of the SiT8009 can be factory-programmed to support three modes: Output Enable (OE), standby (ST) or No Connect (NC). These modes can also be programmed with the Time Machine using field programmable devices.

Output Enable (OE) Mode

In the OE mode, applying logic Low to the OE pin only disables the output driver and puts it in Hi-Z mode. The core of the device continues to operate normally. Power consumption is reduced due to the inactivity of the output. When the OE pin is pulled High, the output is typically enabled in <1 μs .

Standby (ST) Mode

In the \overline{ST} mode, a device enters into the standby mode when Pin 1 pulled Low. All internal circuits of the device are turned off. The current is reduced to a standby current, typically in the range of a few μA . When \overline{ST} is pulled High, the device goes through the "resume" process, which can take up to 5 ms.

No Connect (NC) Mode

In the NC mode, the device always operates in its normal mode and outputs the specified frequency regardless of the logic level on pin 1.

Table 12 below summarizes the key relevant parameters in the operation of the device in OE, \overline{ST} , or NC mode.

Table 12. OE vs. ST vs. NC

	OE	ST	NC
Active current 125 MHz (max, 1.8 V)	5.6 mA	5.6 mA	5.6 mA
OE disable current (max. 1.8 V)	4.0 mA	N/A	N/A
Standby current (typical 1.8 V)	N/A	0.6 uA	N/A
OE enable time at 125 MHz (max)	124 ns	N/A	N/A
Resume time from standby (max, all frequency)	N/A	5 ms	N/A
Output driver in OE disable/standby mode	High Z	weak pull-down	N/A

Output on Startup and Resume

The SiT8009 comes with gated output. Its clock output is accurate to the rated frequency stability within the first pulse from initial device startup or resume from the standby mode.

In addition, the SiT8009 has NO RUNT, NO GLITCH output during startup or resume as shown in the waveform captures in Figure 17 and Figure 18.

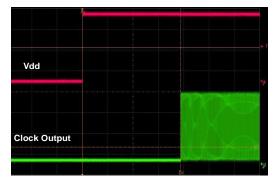


Figure 17. Startup Waveform vs. Vdd

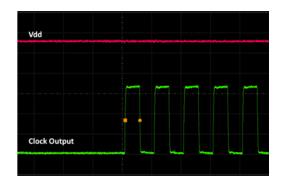


Figure 18. Startup Waveform vs. Vdd (Zoomed-in View of Figure 17)

Instant Samples with Time Machine and Field Programmable Oscillators

SiTime supports a field programmable version of the SiT8009 high frequency, high temperature oscillator for fast prototyping and real time customization of features. The field programmable devices (FP devices) are available for all five standard SiT8009 package sizes and can be configured to one's exact specification using the Time Machine II, an USB powered MEMS oscillator programmer.

Customizable Features of the SiT8009 FP Devices Include

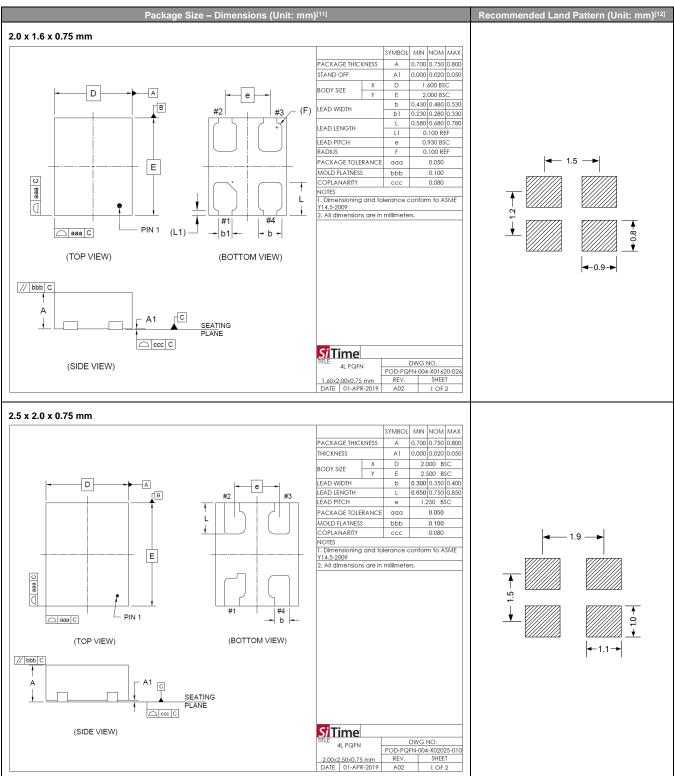
- Frequencies between 115 MHz 137 MHz
- Three frequency stability options, ±20 ppm, ±25 ppm, ±50 ppm
- Two operating temperatures, -20 to 70°C or -40 to 85°C
- Six supply voltage options, 1.8 V, 2.5 V, 2.8 V, 3.0 V, 3.3 V and 2.25 to 3.63 V continuous
- Output drive strength
- OE, ST, or NC mode

For more information regarding SiTime's field programmable solutions, see Time Machine II and Field Programmable Oscillators.

SiT8009 is factory-programmed per customer ordering codes for volume delivery.

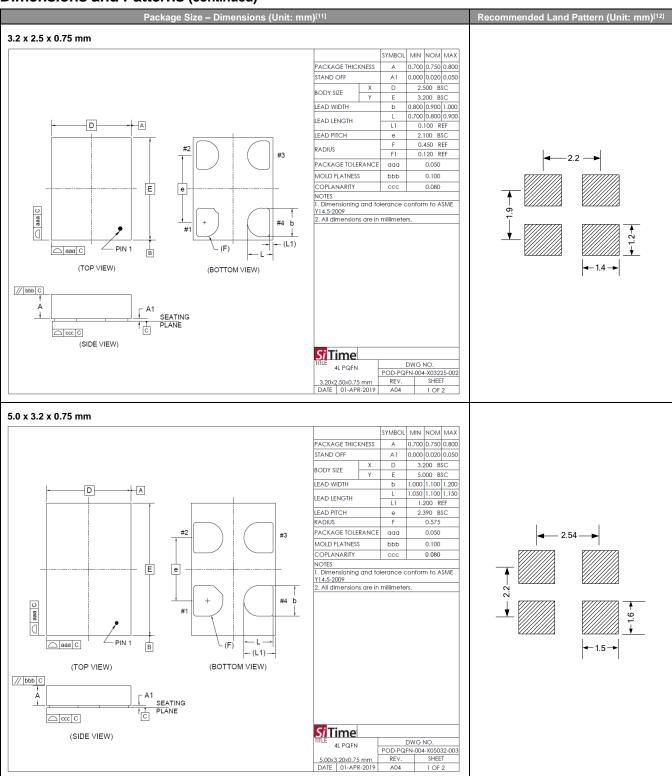


Dimensions and Patterns



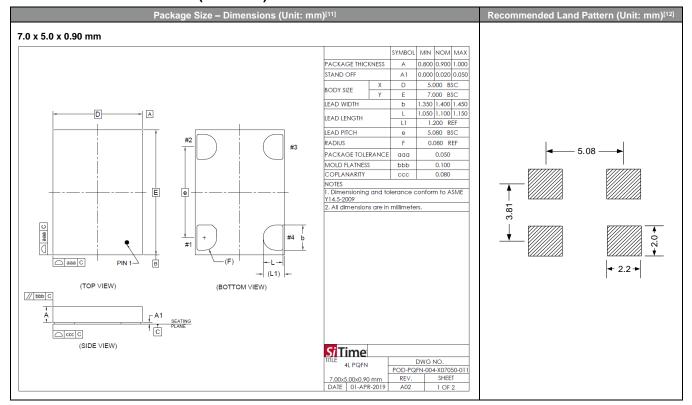


Dimensions and Patterns (continued)





Dimensions and Patterns (continued)



Notes:

- 11. Top marking: Y denotes manufacturing origin and XXXX denotes manufacturing lot number. The value of "Y" will depend on the assembly location of the device
- 12. A capacitor of value 0.1 μF or higher between Vdd and GND is required.



Ordering Information

The Part No. Guide is for reference only.

To customize and build an exact part number, use the SiTime Part Number Generator.

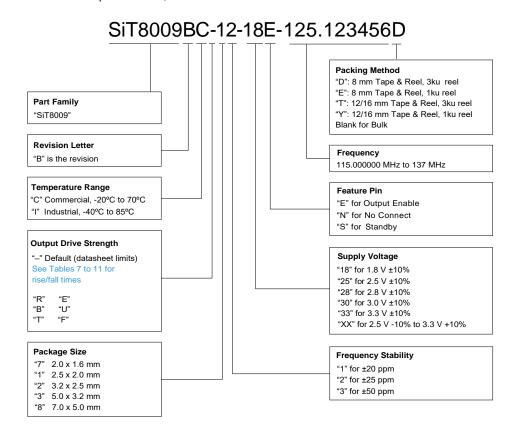


Table 13. Ordering Codes for Supported Tape & Reel Packing Method

Device Size (mm x mm)	16 mm T&R (3ku)	16 mm T&R (1ku)	12 mm T&R (3ku)	12 mm T&R (1ku)	8 mm T&R (3ku)	8 mm T&R (1ku)
2.0 x 1.6	-	-	-	-	D	E
2.5 x 2.0	_	-	-	-	D	E
3.2 x 2.5	-	-	-	-	D	E
5.0 x 3.2	-	-	Т	Υ	-	-
7.0 x 5.0	Т	Υ	-	-	-	-



Table 14. Additional Information

Document Description		Download Link	
Time Machine II MEMS oscillator programmer		http://www.sitime.com/support/time-machine-oscillator-programmer	
Field Programmable Oscillators	Devices that can be programmable in the field by Time Machine II	http://www.sitime.com/products/field-programmable-oscillators	
Manufacturing Notes	Tape & Reel dimension, reflow profile and other manufacturing related info	https://www.sitime.com/sites/default/files/gated/Manufacturing-Notes- for-SiTime-Products.pdf	
Qualification Reports	RoHS report, reliability reports, composition reports	http://www.sitime.com/support/quality-and-reliability	
Performance Reports Additional performance data such as phase noise, current consumption and jitter for selected frequencies		http://www.sitime.com/support/performance-measurement-report	
Termination Techniques	Termination design recommendations	http://www.sitime.com/support/application-notes	
Layout Techniques	Layout recommendations	http://www.sitime.com/support/application-notes	

Table 15. Revision History

Revision	Release Date	Change Summary	
1.0	10-Jun-2014	Final production release	
1.01	7-May-2015	Revised the Electrical Characteristics, Timing Diagrams and Performance Plots Revised 2016 package diagram	
1.02	18-Jun-2015	Added 16 mm T&R information to Table 13 Revised 12 mm T&R information to Table 13	
1.03	30-Aug-2016	Revised part number example in the ordering information	
1.04	9-Jan-2018	Updated logo and company address, other page layout changes Revised 2520 package land pattern	
1.05	9-Jul-2020	Updated ordering information with "YY" supply voltage option Updated ordering information with note	
1.06	15-Mar-2021	Updated hyperlinks, trademarks and changed rev table date format Updated Dimensions and Patterns drawings Removed "YY" supply voltage option from Ordering Information	
1.07	1-Jan-2023	Updated company disclaimer, links, references and icons	

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For aerospace and defense applications, SiTime recommends using only ${\tt Endura^{TM}}$ ruggedized products.

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Supplemental Information

The Supplemental Information section is not part of the datasheet and is for informational purposes only.



Best Reliability

Silicon is inherently more reliable than quartz. Unlike quartz suppliers, SiTime has in-house MEMS and analog CMOS expertise, which allows SiTime to develop the most reliable products. Figure 1 shows a comparison with quartz technology.

Why is SiTime Best in Class:

- SiTime's MEMS resonators are vacuum sealed using an advanced EpiSeal[®] process, which eliminates foreign particles and improves long term aging and reliability
- World-class MEMS and CMOS design expertise

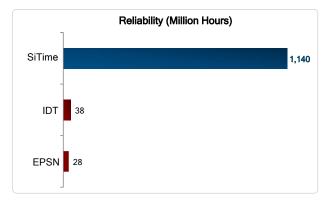


Figure 1. Reliability Comparison[1]

Best Aging

Unlike quartz, MEMS oscillators have excellent long term aging performance which is why every new SiTime product specifies 10-year aging. A comparison is shown in Figure 2.

Why is SiTime Best in Class:

- SiTime's MEMS resonators are vacuum sealed using an advanced EpiSeal[®] process, which eliminates foreign particles and improves long term aging and reliability
- Inherently better immunity of electrostatically driven MEMS resonator

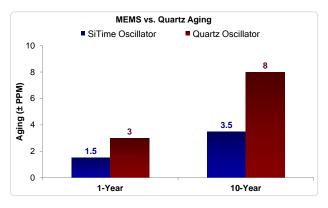


Figure 2. Aging Comparison^[2]

Best Electro Magnetic Susceptibility (EMS)

SiTime's oscillators in plastic packages are up to 54 times more immune to external electromagnetic fields than quartz oscillators as shown in Figure 3.

Why is SiTime Best in Class:

- Internal differential architecture for best common mode noise rejection
- Electrostatically driven MEMS resonator is more immune to EMS

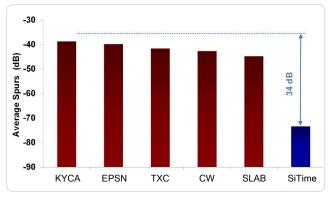


Figure 3. Electro Magnetic Susceptibility (EMS)[3]

Best Power Supply Noise Rejection

SiTime's MEMS oscillators are more resilient against noise on the power supply. A comparison is shown in Figure 4.

Why is SiTime Best in Class:

- On-chip regulators and internal differential architecture for common mode noise rejection
- MEMS resonator is paired with advanced analog CMOS IC

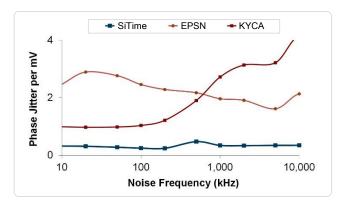


Figure 4. Power Supply Noise Rejection^[4]



Best Vibration Robustness

High-vibration environments are all around us. All electronics, from handheld devices to enterprise servers and storage systems are subject to vibration. Figure 5 shows a comparison of vibration robustness.

Why is SiTime Best in Class:

- The moving mass of SiTime's MEMS resonators is up to 3000 times smaller than quartz
- Center-anchored MEMS resonator is the most robust design

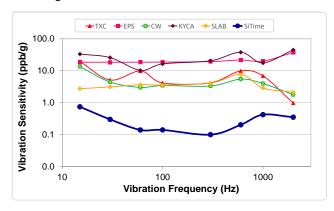


Figure 5. Vibration Robustness^[5]

Figure labels:

- TXC = TXC
- Epson = EPSN
- Connor Winfield = CW
- Kyocera = KYCA
- SiLabs = SLAB
- SiTime = EpiSeal MEMS

Best Shock Robustness

SiTime's oscillators can withstand at least 50,000~g shock. They all maintain their electrical performance in operation during shock events. A comparison with quartz devices is shown in Figure 6.

Why is SiTime Best in Class:

- The moving mass of SiTime's MEMS resonators is up to 3000 times smaller than quartz
- Center-anchored MEMS resonator is the most robust design

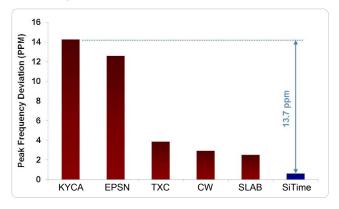


Figure 6. Shock Robustness^[6]

Silicon MEMS Outperforms Quartz



Notes:

- 1. Data source: Reliability documents of named companies.
- 2. Data source: SiTime and quartz oscillator devices datasheets.
- 3. Test conditions for Electro Magnetic Susceptibility (EMS):
 - According to IEC EN61000-4.3 (Electromagnetic compatibility standard)
 - Field strength: 3V/m
 - Radiated signal modulation: AM 1 kHz at 80% depth
 - Carrier frequency scan: 80 MHz 1 GHz in 1% steps
 - Antenna polarization: Vertical
 - DUT position: Center aligned to antenna

Devices used in this test:

Label	Manufacturer	Part Number	Technology
EpiSeal MEMS	SiTime	SiT9120AC-1D2-33E156.250000	MEMS + PLL
EPSN	Epson	EG-2102CA156.2500M-PHPAL3	Quartz, SAW
TXC	TXC	BB-156.250MBE-T	Quartz, 3 rd Overtone
CW	Conner Winfield	P123-156.25M	Quartz, 3 rd Overtone
KYCA	AVX Kyocera	KC7050T156.250P30E00	Quartz, SAW
SLAB	SiLab	590AB-BDG	Quartz, 3 rd Overtone + PLL

4. 50 mV pk-pk Sinusoidal voltage.

Devices used in this test:

Label	Manufacturer	Part Number	Technology
EpiSeal MEMS	SiTime	SiT8208AI-33-33E-25.000000	MEMS + PLL
NDK	NDK	NZ2523SB-25.6M	Quartz
KYCA	AVX Kyocera	KC2016B25M0C1GE00	Quartz
EPSN	Epson	SG-310SCF-25M0-MB3	Quartz

5. Devices used in this test:

same as EMS test stated in Note 3.

- 6. Test conditions for shock test:
 - MIL-STD-883F Method 2002
 - Condition A: half sine wave shock pulse, 500-g, 1ms
 - Continuous frequency measurement in 100 µs gate time for 10 seconds

Devices used in this test:

same as EMS test stated in Note 3.

7. Additional data, including setup and detailed results, is available upon request to qualified customer. Please contact productsupport@sitime.com.